

Summary of key points

5. In the conventional forward converter, the transformer is reset while the transistor is off. The transformer magnetizing inductance operates in the discontinuous conduction mode, and the maximum duty cycle is limited.
6. The flyback converter is based on the buck-boost converter. The flyback transformer is actually a two-winding inductor, which stores and transfers energy.
7. The transformer turns ratio is an extra degree-of-freedom which the designer can choose to optimize the converter design. Use of a computer spreadsheet is an effective way to determine how the choice of turns ratio affects the component voltage and current stresses.
8. Total active switch stress, and active switch utilization, are two simplified figures-of-merit which can be used to compare the various converter circuits.

Key

Summary of chapter 4

only Δt for parasitics

5. Majority carrier devices, including the MOSFET and Schottky diode, exhibit very fast switching times, controlled essentially by the charging of the device capacitances. However, the forward voltage drops of these devices increases quickly with increasing breakdown voltage.

6. Minority carrier devices, including the BJT, IGBT, and thyristor family, can exhibit high breakdown voltages with relatively low forward voltage drop. However, the switching times of these devices are longer, and are controlled by the times needed to insert or remove stored minority charge.

7. Energy is lost during switching transitions, due to a variety of mechanisms. The resulting average power loss, or switching loss, is equal to this energy loss multiplied by the switching frequency. Switching loss imposes an upper limit on the switching frequencies of practical converters.

Summary of chapter 4

8. The diode and inductor present a “clamped inductive load” to the transistor. When a transistor drives such a load, it experiences high instantaneous power loss during the switching transitions. An example where this leads to significant switching loss is the IGBT and the “current tail” observed during its turn-off transition.
9. Other significant sources of switching loss include diode stored charge and energy stored in certain parasitic capacitances and inductances. Parasitic ringing also indicates the presence of switching loss.

Summary of chapter 4

1. How an SPST ideal switch can be realized using semiconductor devices depends on the polarity of the voltage which the devices must block in the off-state, and on the polarity of the current which the devices must conduct in the on-state.
2. Single-quadrant SPST switches can be realized using a single transistor or a single diode, depending on the relative polarities of the off-state voltage and on-state current.
3. Two-quadrant SPST switches can be realized using a transistor and diode, connected in series (bidirectional-voltage) or in anti-parallel (bidirectional-current). Several four-quadrant schemes are also listed here.
4. A "synchronous rectifier" is a MOSFET connected to conduct reverse current, with gate drive control as necessary. This device can be used where a diode would otherwise be required. If a MOSFET with sufficiently low R_{on} is used, reduced conduction loss is obtained.

$$I_{ON} R_{DS} \leq 0.7V$$

75
70 A 10mΩ